

Substitute for form 1449A/PTO

Complete if Known

(use as many sheets as necessary)

Sheet

1

of

1

Application Number

10/627,228

Filing Date

July 25, 2003

First Named Inventor

Moghadam et. al.

Art Unit

~~Unassigned~~ 1753

Examiner Name

Unassigned → Versteck

Attorney Docket Number

A7632/Т49100

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

**Examiner
Signature**

Date Considered

March 31, 2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Kind Codes of U.S. Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for**
Patents, Washington, DC 20231
PA 3260951 v1

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Complete if Known

Application Number

~~Unassigned~~ 10/607228

Filing Date

Filed Herewith

First Named Inventor

Moghadam, Farhad K., et. al.

Art Unit

~~Unassigned~~ 1753

Examiner Name

Unassigned	VerSteg
-----------------------	---------

Attorney Docket Number

A7632/T49100

Page

1

of

2

Class

sub class,

[illegible]

Adams

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Class Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T°
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
SHV	AM	WO	01/40541	A1	06-07-2001	C23C	16/40	<input type="checkbox"/>
SHV	AN	WO	00/61833	A1	10-19-2000	C23C	16/50	<input type="checkbox"/>
SHV	AO	WO	01/66832	A2	09-13-2001	C23C	16/44	<input type="checkbox"/>
SHV	AP	WO	00/54320	A1	09-14-2000	H01L	21/44	<input type="checkbox"/>
SHV	AQ	EP	526 779	B1	02-10-1993	C23C	16/04	<input type="checkbox"/>
SHV	AR	EP	442 490	A1	08-21-1991	C30A	25/02	<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>

**Examiner
Signature**

Date
Considered

March 31, 2015

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.


¹ Applicant's unique citation designation number (optional). ² Kind Codes of U.S. Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	Unassigned 12/627208
		Filing Date	Filed Herewith
		First Named Inventor	Moghadam, Farhad K., et. al.
		Art Unit	Unassigned 1753
		Examiner Name	Unassigned VerSteg
		Attorney Docket Number	A7632/T49100
Page	2	of	2

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SHV	AS	"Atomic Layer Deposition" by Physical Inorganic Chemistry, Institute of Applied Synthetic Chemistry, downloaded from website http://www.ias.tuwien.ac.at/research/fghh/research/pic_research_ald.html on 7/23/02	
SHV	AT	GEORGE et al., "Atomic layer controlled deposition of SiO ₂ and Al ₂ O ₃ using ABAB... binary reaction sequence chemistry," <i>Applied Surface Science</i> , 82/83:460-467 (1994).	
SHV	AU	GEORGE et al., "Surface Chemistry for Atomic Layer Growth," <i>J. Phys. Chem.</i> , 100(31):13121-13131 (1996).	
SHV	AV	KLAUS et al., "Atomic Layer Deposition of SiO ₂ Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," <i>Surface Review and Letters</i> , 6(3/4):435-448 (1999).	
SHV	AW	KLAUS et al., "Atomic layer controlled growth of SiO ₂ films using binary reaction sequence chemistry," <i>Appl. Phys. Lett.</i> , 70(9):1092-1094 (1997).	
SHV	AX	MORISHITA et al., "New substances for atomic-layer deposition of silicon dioxide," <i>J. Non-Crystalline Solids</i> , 187:66-69 (1995).	
SHV	AY	WISE et al., "Diethyldiethoxysilane as a New Precursor for SiO ₂ Growth on Silicon," from <i>Gas-Phase and Surface Chemistry in electronic Materials Processing</i> , Mountziaris et al., eds., from Symposium held 11/29/93 thru 12/2/93 in Boston Massachusetts, pages 37-43.	
SHV	AZ	YAMAGUCHI et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content," <i>Applied Surface Science</i> , 130-132:202-207 (1998).	

Examiner Signature		Date Considered	March 31, 2005
--------------------	--	-----------------	----------------

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.